

TC74HC51AP/AF/AFN

DUAL 2 WIDE-2 INPUT AND/OR INVERT GATE

The TC74HC51A is a high speed CMOS 2-WIDE 2-INPUT/3-INPUT AND/OR/INVERT GATE fabricated with silicon gate C²MOS technology.

It achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation.

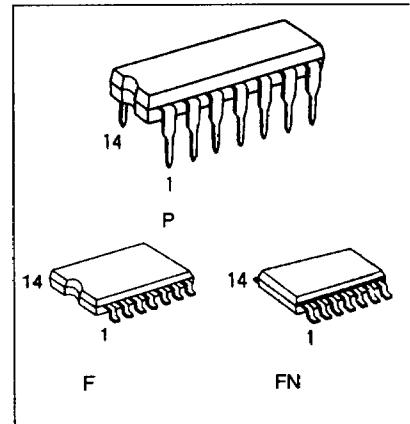
It contains a 2-WIDE 2-INPUT AND/OR/INVERT GATE and a 2-WIDE 3-INPUT AND/OR/INVERT GATE.

The internal circuit is composed of 3 stages (2-INPUT) or 5 stages (3-INPUT) including buffer outputs, which provide high noise immunity and stable output.

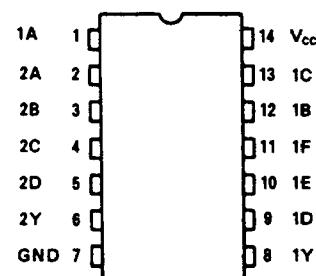
All inputs are equipped with protection circuits against static discharge or transient excess voltage.

FEATURES:

- High Speed $t_{PD} = 10 \text{ ns} (\text{Typ.})$ at $V_{CC} = 5V$
- Low Power Dissipation $I_{CC} = 1 \mu A (\text{Max.})$ at $T_a = 25^\circ C$
- High Noise Immunity $V_{NH} = V_{NL} = 28\% V_{CC} (\text{Min.})$
- Output Drive Capability 10 LSTTL Loads
- Symmetrical Output Impedance $\cdots |I_{OH}| = I_{OL} = 4mA (\text{Min.})$
- Balanced Propagation Delays $\cdots t_{PLH} = t_{PHL}$
- Wide Operating Voltage Range $\cdots V_{CC} (\text{opr}) = 2V \sim 6V$
- Pin and Function Compatible with 74LS51

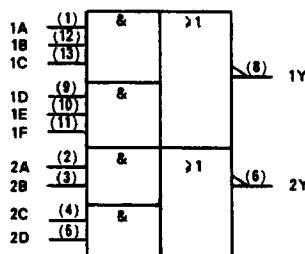


PIN ASSIGNMENT



(TOP VIEW)

IEC LOGIC SYMBOL



ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V_{CC}	-0.5 ~ 7	V
DC Input Voltage	V_{IN}	-0.5 ~ V_{CC} + 0.5	V
DC Output Voltage	V_{OUT}	-0.5 ~ V_{CC} + 0.5	V
Input Diode Current	I_{IK}	± 20	mA
Output Diode Current	I_{OK}	± 20	mA
DC Output Current	I_{OUT}	± 25	mA
DC V_{CC} /Ground Current	I_{CC}	± 50	mA
Power Dissipation	P_D	500(DIP)* / 180(MFP)	mW
Storage Temperature	T_{stg}	-65 ~ 150	°C
Lead Temperature 10sec	T_L	300	°C

*500mW in the range of $T_a = -40^{\circ}\text{C} \sim 65^{\circ}\text{C}$. From $T_a = 65^{\circ}\text{C}$ to 85°C a derating factor of $-10\text{mW}/^{\circ}\text{C}$ shall be applied until 300mW.

RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V_{CC}	2 ~ 6	V
Input Voltage	V_{IN}	0 ~ V_{CC}	V
Output Voltage	V_{OUT}	0 ~ V_{CC}	V
Operating Temperature	T_{opr}	-40 ~ 85	°C
Input Rise and Fall Time	t_r, t_f	0 ~ 1000($V_{CC}=2.0\text{V}$) 0 ~ 500($V_{CC}=4.5\text{V}$) 0 ~ 400($V_{CC}=6.0\text{V}$)	ns

DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	Ta=25°C			Ta=-40 ~ 85°C		UNIT		
			V_{CC}	MIN.	TYP.	MAX.	MIN.			
High-Level Input Voltage	V_{IH}		2.0	1.5	—	—	1.5	—	V	
			4.5	3.15	—	—	3.15	—		
			6.0	4.2	—	—	4.2	—		
Low-Level Input Voltage	V_{IL}		2.0	—	—	—	0.5	—	V	
			4.5	—	—	—	1.35	—		
			6.0	—	—	—	1.8	—		
High-Level Output Voltage	V_{OH}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -20\mu\text{A}$	2.0	1.9	2.0	—	1.9	—	V
			$I_{OH} = -4\text{ mA}$	4.5	4.4	4.5	—	4.4	—	
			$I_{OH} = -5.2\text{mA}$	6.0	5.9	6.0	—	5.9	—	
Low-Level Output Voltage	V_{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 20\mu\text{A}$	2.0	—	0.0	0.1	—	0.1	V
			$I_{OL} = 4\text{ mA}$	4.5	—	0.0	0.1	—	0.1	
			$I_{OL} = 5.2\text{mA}$	6.0	—	0.0	0.1	—	0.1	
Input Leakage Current	I_{IN}	$V_{IN} = V_{CC}$ or GND	6.0	—	—	± 0.1	—	± 1.0	μA	
Quiescent Supply Current	I_{CC}	$V_{IN} = V_{CC}$ or GND	6.0	—	—	1.0	—	10.0	μA	

AC ELECTRICAL CHARACTERISTICS($C_L=15\text{pF}$, $V_{CC}=5\text{V}$, $T_a=25^\circ\text{C}$, Input $t_r=t_f=6\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Output Transition Time	t_{TLH} t_{THL}		—	4	8	ns
Propagation Delay Time	t_{PLH} t_{PHL}		—	10	17	

AC ELECTRICAL CHARACTERISTICS($C_L=50\text{pF}$, Input $t_r=t_f=6\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION	$T_a=25^\circ\text{C}$			$T_a=-40 \sim 85^\circ\text{C}$		UNIT
			V_{CC}	MIN.	TYP.	MAX.	MIN.	
Output Transition Time	t_{TLH}		2.0	—	30	75	—	95
	t_{THL}		4.5	—	8	15	—	19
			6.0	—	7	13	—	16
Propagation Delay Time	t_{PLH}		2.0	—	39	100	—	125
	t_{PHL}		4.5	—	13	20	—	25
			6.0	—	11	17	—	21
Input Capacitance	C_{IN}		—	—	5	10	—	10
Power Dissipation Capacitance	$C_{PD(1)}$		—	—	35	—	—	—

Note (1) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

$$I_{CC(\text{avg})} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 2 (\text{per Gate})$$

TRUTH TABLE

INPUTS						OUTPUT
1A	1B	1C	1D	1E	1F	1Y
H	H	H	X	X	X	L
X	X	X	H	H	H	L
All other combinations						H

X:Don't care

INPUTS				OUTPUT
2A	2B	2C	2D	2Y
H	H	X	X	L
X	X	H	H	L
All other combinations				H

X:Don't care

SYSTEM DIAGRAM

